

SN65MLVD048 四通道 M-LVDS 接收器

1 特性

- 低电压差分 30Ω 至 55Ω 线路接收器，信号传输速率¹高达 250Mbps ；时钟频率高达 125MHz
- 1类接收器具有 25mV 输入阈值迟滞
- 2类接收器提供 100mV 偏移阈值，可检测开路和空闲总线状态
- 宽接收器输入共模电压范围为 -1V 至 3.4V ，允许 2V 接地噪声
- 多点拓扑符合或超过 M-LVDS 标准 TIA/EIA-899
- $V_{cc} \leq 1.5\text{V}$ 时具有高输入阻抗
- 增强型 ESD 保护：针对所有引脚的 7kV HBM
- 48 引脚 7×7 QFN (RGZ)

2 应用

- 通过背板和电缆进行并行多点数据和时钟传输
- 蜂窝基站
- 局端交换机
- 网络交换机和路由器

3 说明

SN65MLVD048 是一款四通道 M-LVDS 接收器。该器件的设计完全符合 TIA/EIA-899 (M-LVDS) 标准，设计经过优化，可在高达 250Mbps 的信号传输速率下运行。每个接收器通道都由一个接收使能 (\overline{RE}) 控制。当 $\overline{RE} = \text{低电平时}$ ，对应的通道被启用；当 $\overline{RE} = \text{高电平时}$ ，对应的通道被禁用。

M-LVDS 标准定义了两种接收器类型，即 1 类和 2 类。1类接收器的阈值以零为中心，迟滞为 25mV ，可防止输入丢失时出现输出振荡；2类接收器使用偏移阈值实现失效防护。对接收器输出端进行压摆率控制以减少与大电流浪涌相关的 EMI 和串扰影响。

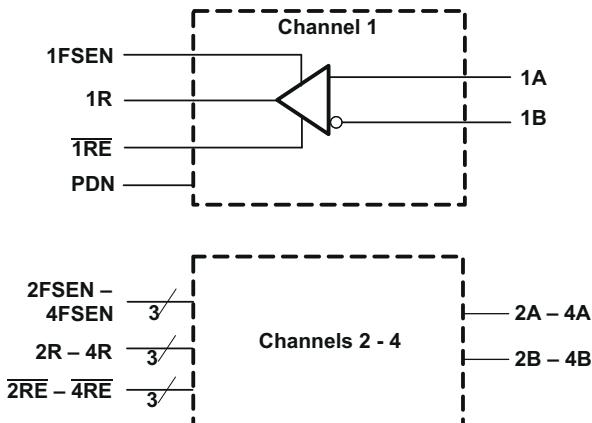
这些器件的额定工作温度范围为 -40°C 至 85°C 。

封装信息

器件型号	封装 ⁽¹⁾	封装尺寸 ⁽²⁾
SN65MLVD048	VQFN (RGZ , 48)	7mm x 7mm

(1) 如需了解更多信息，请参阅 [节 10](#)。

(2) 封装尺寸 (长 × 宽) 为标称值，并包括引脚 (如适用)。



逻辑图 (正逻辑)

¹ 线路的信号传输速率是指每秒钟的电压转换次数，单位为 bps (每秒比特数)。



本资源的原文使用英文撰写。为方便起见，TI 提供了译文；由于翻译过程中可能使用了自动化工具，TI 不保证译文的准确性。为确认准确性，请务必访问 ti.com 参考最新的英文版本 (控制文档)。

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4 Pin Configuration and Functions

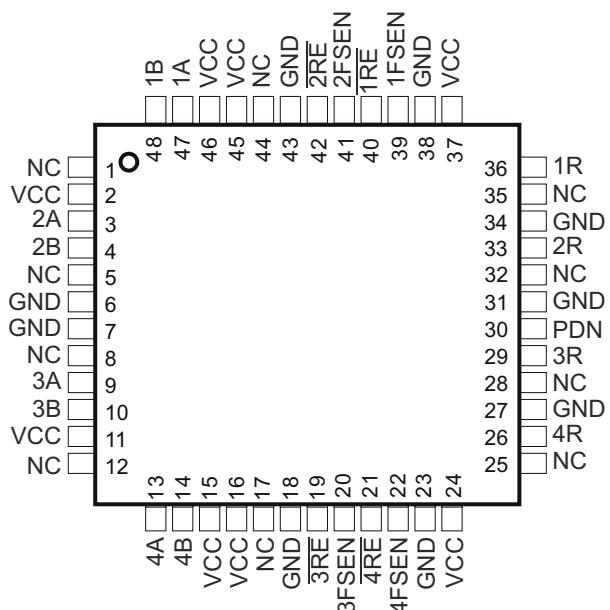


图 4-1. RGZ Package (Top View)

PIN	I/ O ⁽¹⁾	DESCRIPTION
NAME	NO.	
1R - 4R	36, 33, 29, 26	O Data output from receivers
1A - 4A	47, 3, 9, 13	I/O M-LVDS bus non-inverting input/output
1B - 4B	48, 4, 10, 14	I/O M-LVDS bus inverting input/output
GND	6, 7, 18, 23, 27, 31, 34, 38, 43	I Circuit ground. ALL GND pins must be connected to ground.
V _{CC}	2, 11, 15, 16, 24, 37, 45, 46	I Supply voltage. ALL V_{CC} pins must be connected to supply.
1RE - 4RE	40, 42, 19, 21	I Receiver enable, active low, enables individual receivers. When this pin is left floating, internally this pin will be pulled to logic HIGH.
1FSEN - 4FSEN	39, 41, 20, 22	I Failsafe enable pin. When this pin is left floating, internally this pin will be pulled to logic HIGH. This pin enables the Type 2 receiver for the respective channel. xFSEN = L → Type 1 receiver inputs xFSEN = H → Type 2 receiver inputs
PDN	30	I Power Down pin. When this pin is left floating, internally this pin will be pulled to logic LOW. When PDN is HIGH, the device is powered up. When PDN is LOW, the device overrides all other control and powers down. All outputs are Hi-Z
NC	1, 5, 8, 12, 17, 25, 28, 32, 35	Not Connected
NC	44	Not Connected. Internal TI Test pin. This pin must be left unconnected.
PowerPAD™	-	Connected to GND

(1) Signal Types: I = Input, O = Output, I/O = Input or Output.

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) ⁽¹⁾

		MIN	TYP	MAX	UNIT
V _{CC}	Supply voltage range ⁽²⁾	- 0.5		4	V
Input voltage range	RE, FSEN	- 0.5		4	V
	A or B	- 1.8		4	V
Output voltage range	R	- 0.3		4	V
P _D	RE at 0V, C _L = 15pF, V _{ID} = 400mV, 125MHz			339	mW
T _{stg}	Storage Temperature	- 65		150	°C

(1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.

5.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±7000
		Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾	±1500

(1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage	3	3.3	3.6	V
V _{IH}	High-level input voltage	2		V _{CC}	V
V _{IL}	Low-level input voltage	GND		0.8	V
V _A or V _B	Voltage at any bus terminal	- 1.4		3.8	V
V _{ID}	Magnitude of differential input voltage	0.05		V _{CC}	V
V _{IC}	Differential common-mode input voltage	- 1		3.4	V
R _L	Differential load resistance	30	50		Ω
1/t _{UI}	Signaling rate			250	Mbps
T _A	Operating free-air temperature	- 40		85	°C

5.4 Package Dissipation Ratings

PACKAGE ⁽¹⁾	PCB TYPE	T _A ≤ 25°C POWER RATING	DERATING FACTOR ⁽²⁾ ABOVE T _A = 25°C	T _A = 85°C POWER RATING
48-Pin QFN (RGZ)	Low-K	1298 mW	12.98 mW/°C	519 mW
	High-K	3448 mW	34.48 mW/°C	1379 mW

(1) The thermal dissipations are in the consideration of soldering down the powerPAD without via on each type of boards.

(2) This is the inverse of the junction-to-ambient thermal resistance when board-mounted and with no air flow.

5.5 Thermal Information

THERMAL METRIC ⁽¹⁾		RGZ	UNIT
		48-Pins	
R _{θJA}	Junction-to-ambient thermal resistance	25.4	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	15.1	°C/W
R _{θJB}	Junction-to-board thermal resistance	8.7	°C/W
ψ _{JT}	Junction-to-top characterization parameter	0.2	°C/W
ψ _{JB}	Junction-to-board characterization parameter	8.7	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	1.4	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC package thermal metrics](#) application report.

5.6 Device Electrical Characteristics

over recommended operating conditions (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
I _{CC} Supply current	V _E at 0V for all channels C _L = 15pF, V _{ID} = 400mV, 125MHz		86	94	mA
Power down	PDN = L		0.75	1.5	mA

(1) All typical values are at 25°C and with a 3.3V supply voltage.

5.7 Receiver Electrical Characteristics

over recommended operating conditions (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
V _{IT+} Positive-going differential input voltage threshold	Type 1			35	mV
	Type 2			135	
V _{IT-} Negative-going differential input voltage threshold	Type 1			-35	mV
	Type 2			65	
V _{HYS} Differential input voltage hysteresis (V _{IT+} - V _{IT-})	Type 1			25	mV
	Type 2			0	
V _{OH} High-level output voltage	I _{OH} = ~8mA		2.4		V
V _{OL} Low-level output voltage	I _{OL} = 8mA			0.4	V
I _{IH} High-level input current	V _{IH} = 2V to V _{CC}		-10		µA
I _{IL} Low-level input current	V _{IL} = GND to 0.8V		-10		µA
I _{OZ} High-impedance output current	V _O = 0V or V _{CC}		-10	15	µA
I _A or I _B Receiver input current	One input (V _A or V _B) = -1.4V or 3.8V, Other input = 1.2V		-20	20	µA
I _{AB} Receiver differential input current (I _A - I _B)	V _A = V _B = -1.4V or 3.8V		-4	4	µA
I _{A(OFF)} or I _{B(OFF)} Receiver input current	One input (V _A or V _B) = -1.4V or 3.8V, Other input = 1.2V, V _{CC} = GND or 1.5V		-32	32	µA
I _{AB(OFF)} Receiver power-off differential input current (I _A - I _B)	V _A = V _B = -1.4V or 3.8V, V _{CC} = GND or 1.5V		-4	4	µA
C _A or C _B Input capacitance	V _I = 0.4sin(30E6 π t) + 0.5V, ⁽²⁾ Other input at 1.2V		5		pF
C _{AB} Differential input capacitance	V _{AB} = 0.4sin(30E6 π t) + 0.5V ⁽²⁾			3	pF
C _{A/B} Input capacitance balance, (C _A /C _B)			0.99	1.01	

(1) All typical values are at 25°C and with a 3.3V supply voltage.

- (2) HP4194A impedance analyzer (or equivalent)

5.8 Receiver Switching Characteristics

over recommended operating conditions (unless otherwise noted)

PARAMETER	TEST CONDITIONS		MIN	TYP ⁽¹⁾	MAX	UNIT
t_{PLH}	$C_L = 15\text{pF}$, See 图 6-2		2	6	ns	
t_{PHL}			2	6	ns	
t_r			1	2.3		
t_f			1	2.3	ns	
$t_{sk(p)}$	Pulse skew ($ t_{PHL} - t_{PLH} $)	Type 1	35	270		ps
		Type 2	150	460		
$t_{sk(pp)}$	Part-to-part skew			800		ps
$t_{jit(per)}$	Period jitter, rms (1 standard deviation) ⁽²⁾	All channels switching, 125MHz clock input ⁽³⁾ , See 图 6-4		6	ps	
$t_{jit(c-c)}$	Cycle-to-cycle jitter, rms ⁽²⁾			13	ps	
$t_{jit(det)}$	Deterministic jitter ⁽²⁾	Type 1	800	ps		
		Type 2	945	ps		
$t_{jit(ran)}$	Random jitter ⁽²⁾	Type 1	9	ps		
		Type 2	8	ps		
t_{PZH}	Enable time, high-impedance-to-high-level output	$C_L = 15\text{pF}$, See 图 6-3		15	ns	
t_{PZL}	Enable time, high-impedance-to-low-level output	$C_L = 15\text{pF}$, See 图 6-3		15	ns	
t_{PHZ}	Disable time, high-level-to-high-impedance output	$C_L = 15\text{pF}$, See 图 6-3		10	ns	
t_{PLZ}	Disable time, low-level-to-high-impedance output	$C_L = 15\text{pF}$, See 图 6-3		10	ns	

(1) All typical values are at 25°C and with a 3.3V supply voltage.

(2) Jitter is ensured by design and characterization. Stimulus jitter has been subtracted from the numbers.

(3) $t_r = t_f = 0.5\text{ns}$ (10% to 90%)

5.9 Typical Characteristics

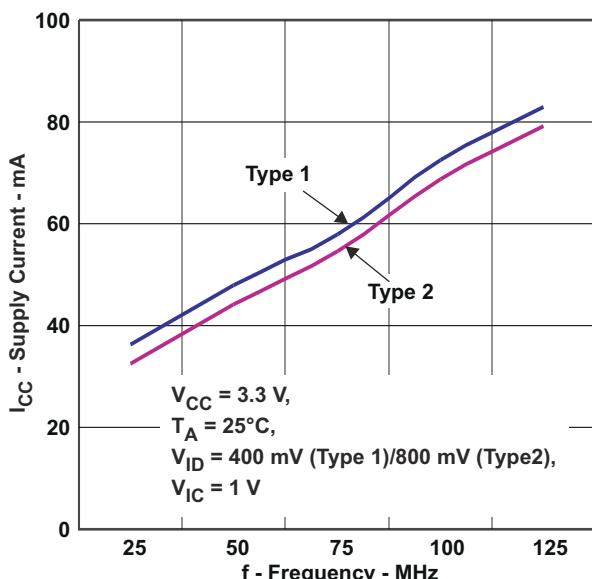


图 5-1. Supply Current vs Frequency

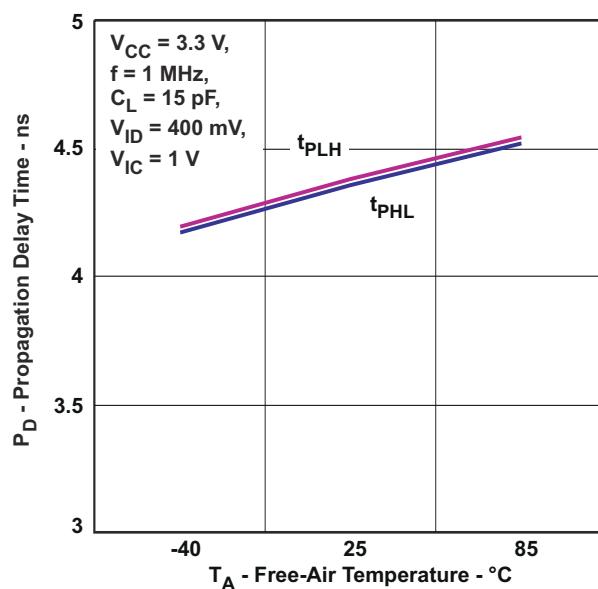


图 5-2. Receiver (Type-1) Propagation Delay Time vs Free-Air Temperature

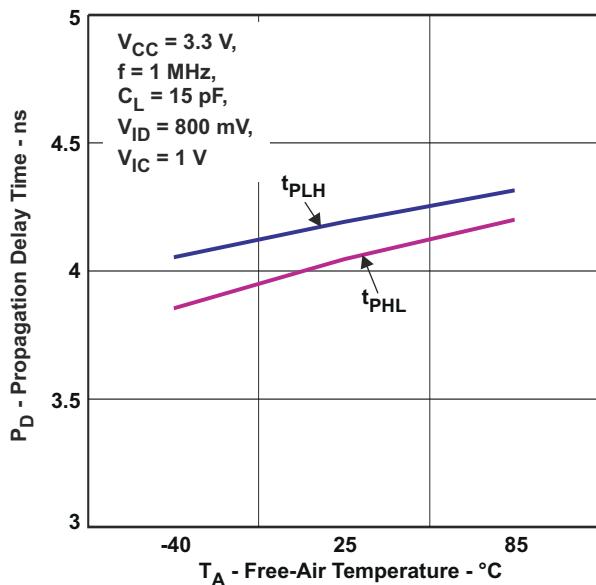


图 5-3. Receiver (Type-2) Propagation Delay Time vs Free-Air Temperature

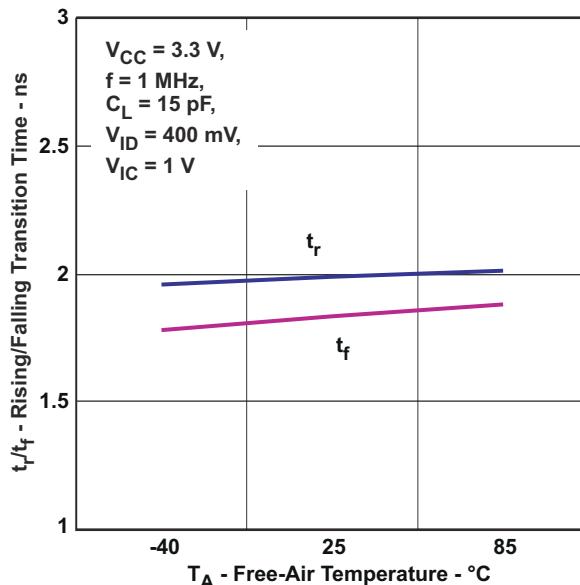


图 5-4. Receiver (Type-1) Transition Time vs Free-Air Temperature

5.9 Typical Characteristics (continued)

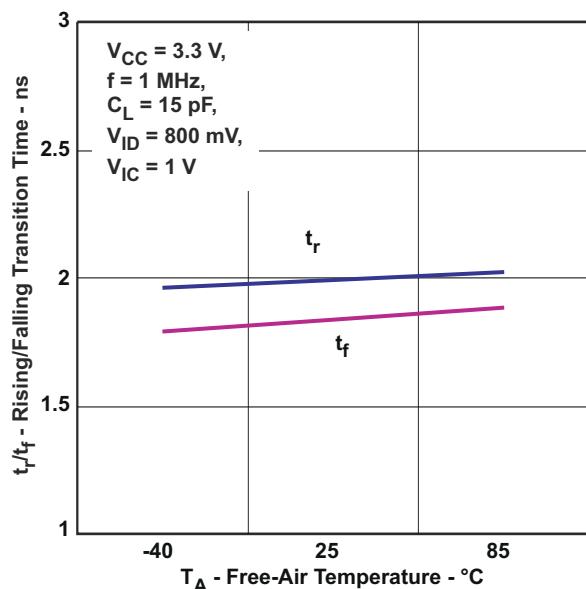


图 5-5. Receiver (Type-2) Transition Time vs Free-Air Temperature

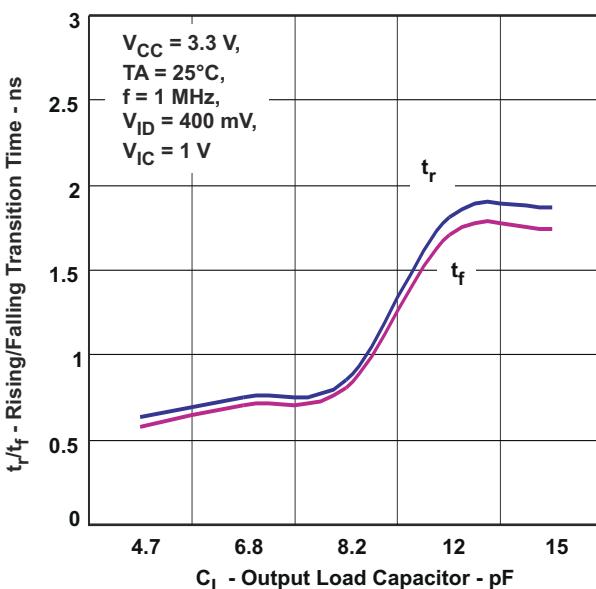


图 5-6. Receiver (Type-1) Transition Time vs Output Load Capacitor

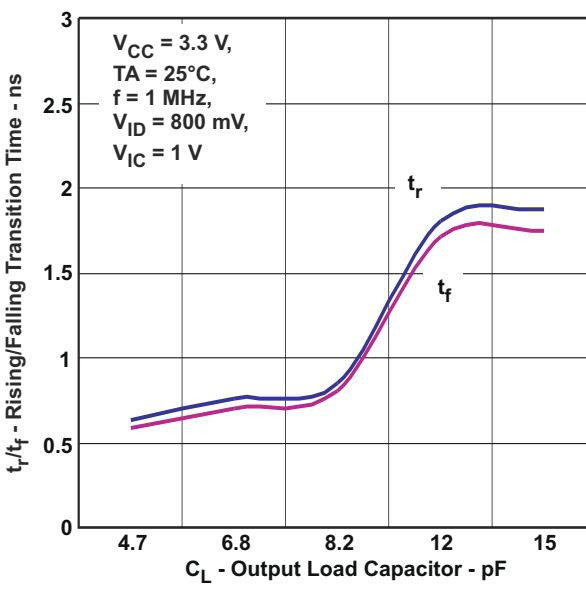


图 5-7. Receiver (Type-2) Transition Time vs Output Load Capacitor

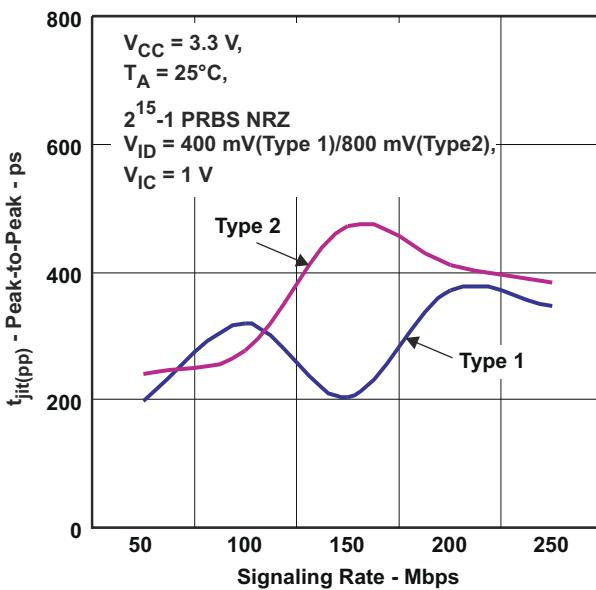
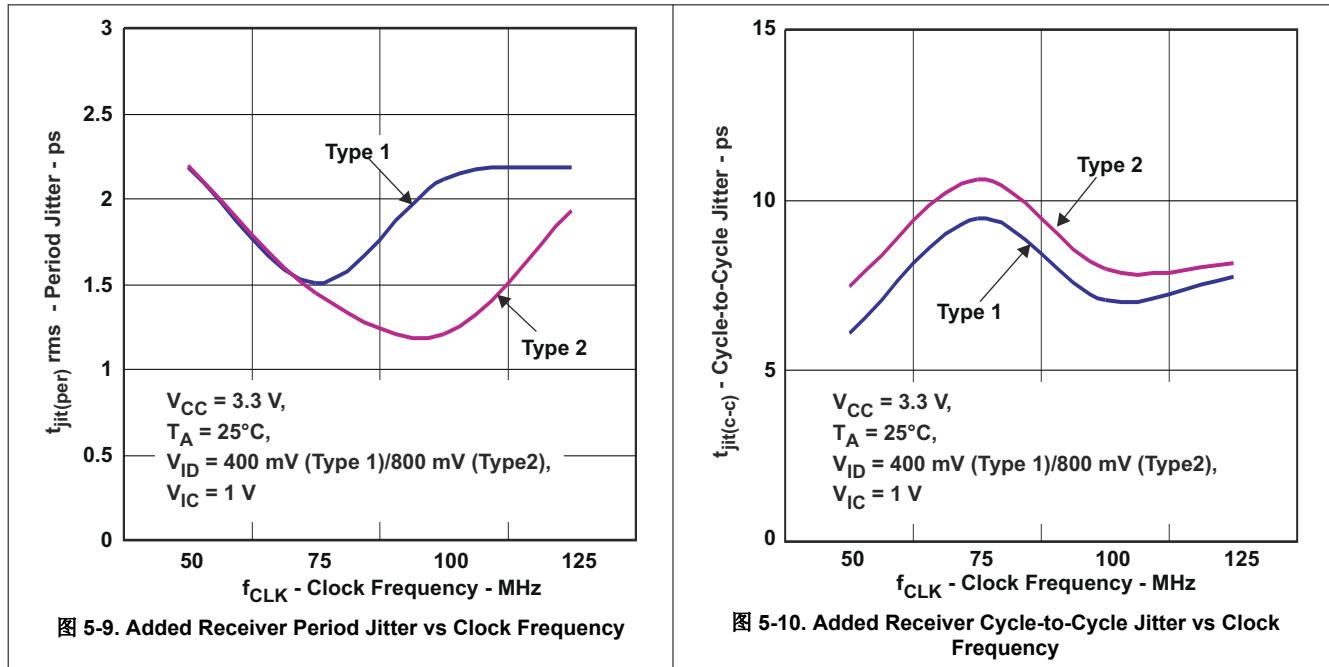


图 5-8. Added Receiver Peak-to-Peak Jitter vs Signaling Rate

5.9 Typical Characteristics (continued)



5.9.1 Eye Patterns

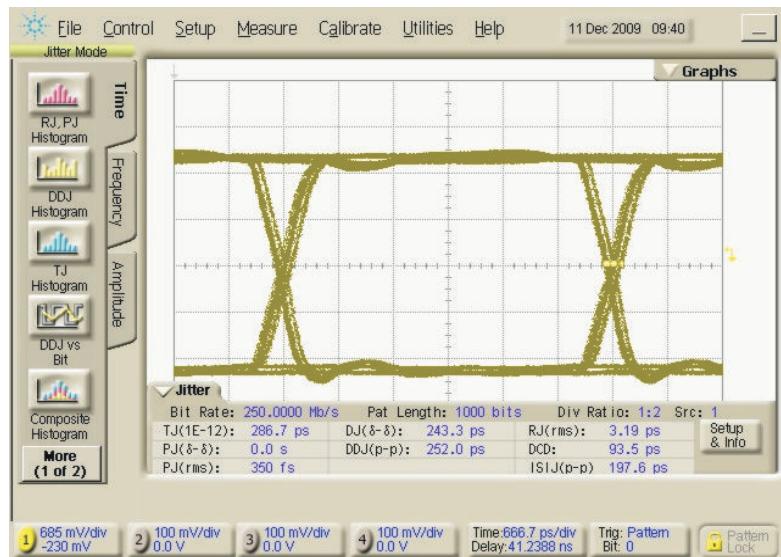


图 5-11. Output ($V_{CC} = 3.3 \text{ V}$, $V_{ID} = 400 \text{ mV}$) 250Mbps $2^{15} - 1$ PRBS, Receiver Type 1

5.9.1 Eye Patterns (continued)

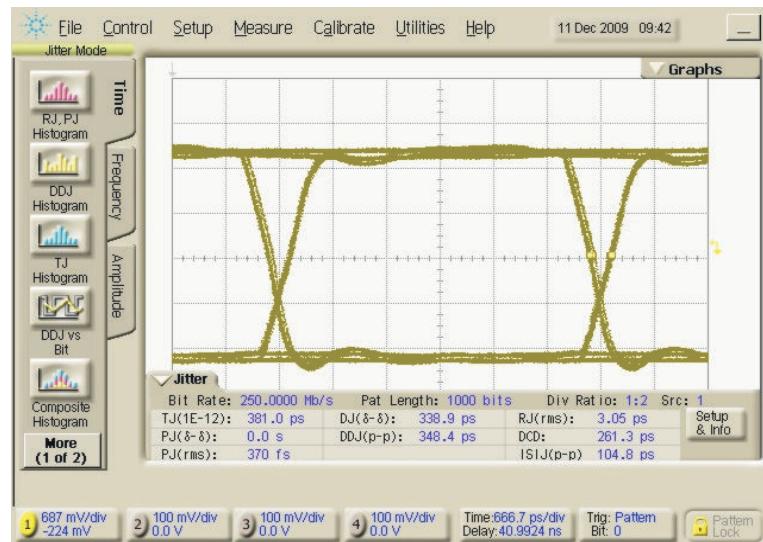


图 5-12. Output ($V_{CC} = 3.3V$, $V_{ID} = 800mV$) 250Mbps $2^{15} - 1$ PRBS, Receiver Type 2

6 Parameter Measurement Information

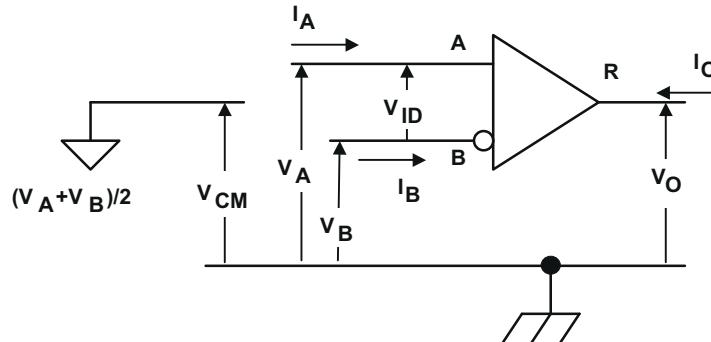


图 6-1. Receiver Voltage and Current Definitions

表 6-1. Type-1 Receiver Input Threshold Test Voltages

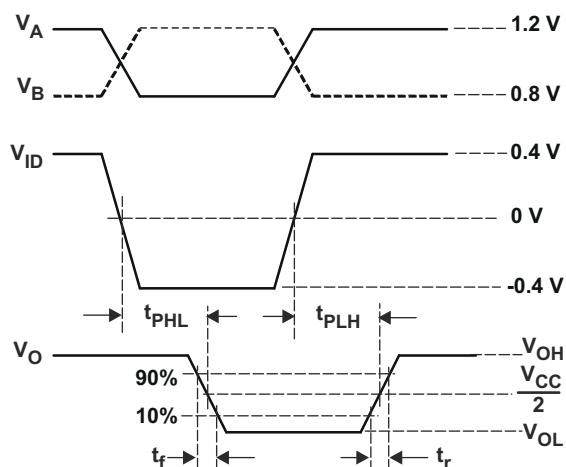
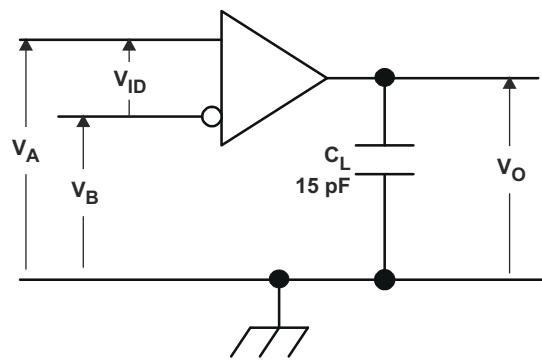
APPLIED VOLTAGES		RESULTING DIFFERENTIAL INPUT VOLTAGE	RESULTING COMMON-MODE INPUT VOLTAGE	RECEIVER OUTPUT ⁽¹⁾
V _{IA}	V _{IB}	V _{ID}	V _{IC}	
2.400	0.000	2.400	1.200	H
0.000	2.400	-2.400	1.200	L
3.400	3.365	0.035	3.3825	H
3.365	3.400	-0.035	3.3825	L
-0.965	-1	0.035	-0.9825	H
-1	-0.965	-0.035	-0.9825	L

(1) H= high level, L = low level, output state assumes receiver is enabled ($\overline{RE} = L$)

表 6-2. Type-2 Receiver Input Threshold Test Voltages

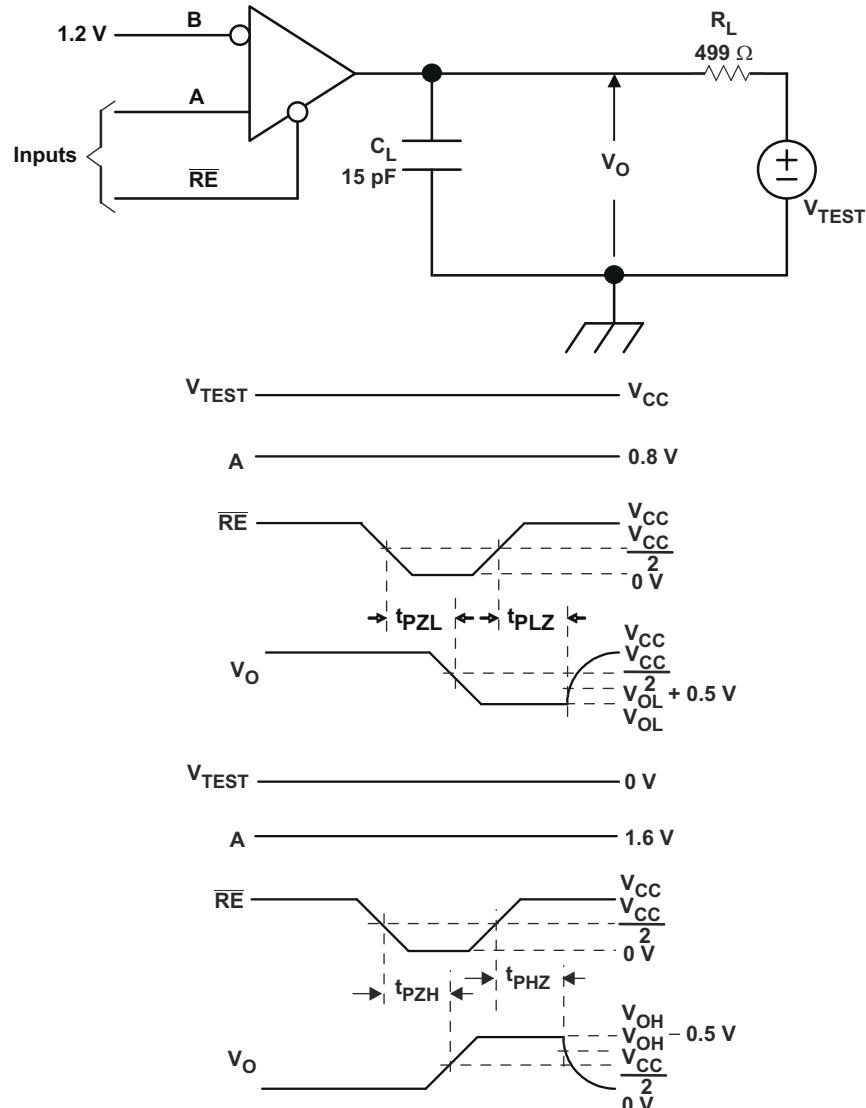
APPLIED VOLTAGES		RESULTING DIFFERENTIAL INPUT VOLTAGE	RESULTING COMMON-MODE INPUT VOLTAGE	RECEIVER OUTPUT ⁽¹⁾
V _{IA}	V _{IB}	V _{ID}	V _{IC}	
2.400	0.000	2.400	1.200	H
0.000	2.400	-2.400	1.200	L
3.400	3.265	0.135	3.3325	H
3.4000	3.335	0.05065	3.3675	L
-0.865	-1	0.135	-0.9325	H
-0.935	-1	0.065	-0.9675	L

(1) H= high level, L = low level, output state assumes receiver is enabled ($\overline{RE} = L$)



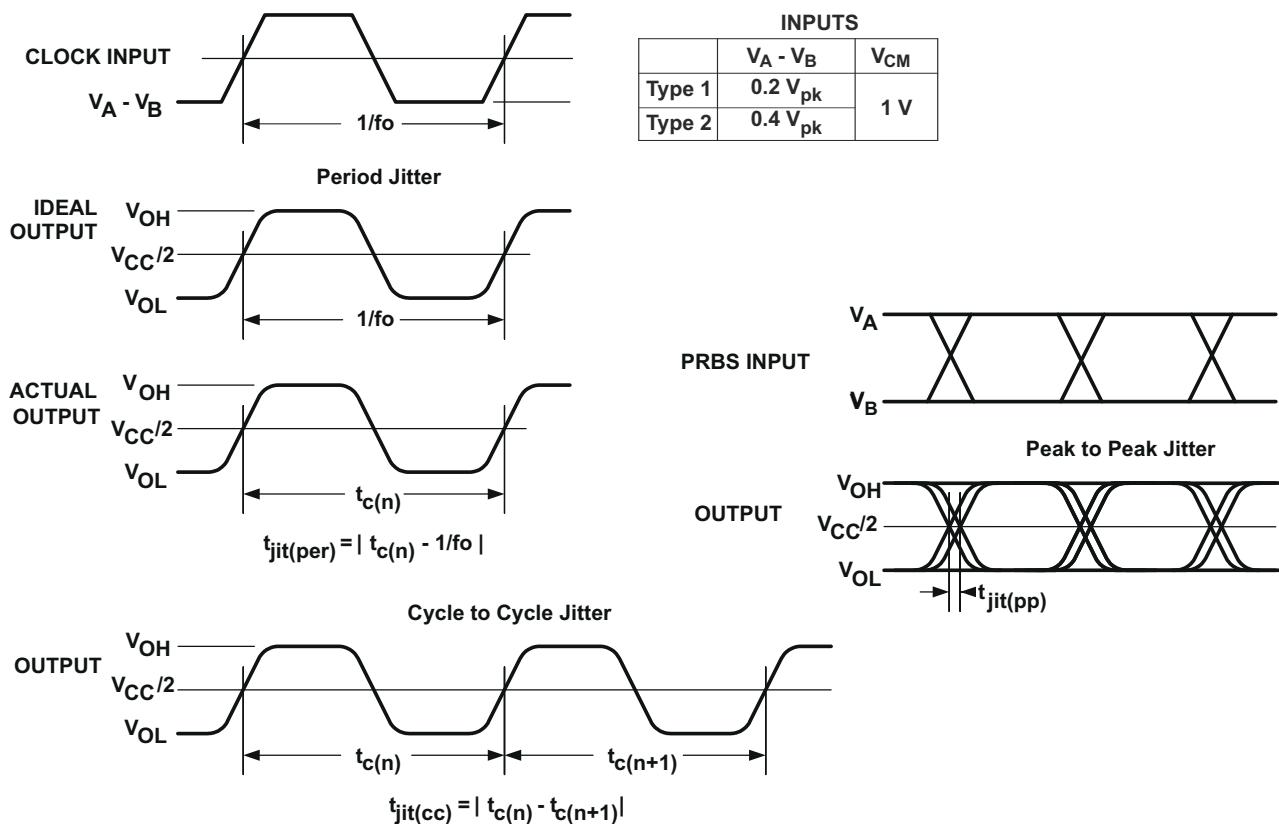
- A. All input pulses are supplied by a generator having the following characteristics: t_f or $t_r \leq 1\text{ns}$, Frequency = 1MHz, duty cycle = $50 \pm 5\%$. C_L is a combination of a 20%-tolerance, low-loss ceramic, surface-mount capacitor and fixture capacitance within 2 cm of the D.U.T.
- B. The measurement is made on test equipment with a $\sim 3\text{dB}$ bandwidth of at least 1GHz.

图 6-2. Receiver Timing Test Circuit and Waveforms



- A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \leq 1\text{ns}$, frequency = 1MHz, duty cycle = $50 \pm 5\%$.
- B. R_L is 1% tolerance, metal film, surface mount, and located within 2 cm of the D.U.T.
- C. C_L is the instrumentation and fixture capacitance within 2 cm of the D.U.T. and $\pm 20\%$. The measurement is made on test equipment with a $\sim 3\text{dB}$ bandwidth of at least 1GHz.

图 6-3. Receiver Enable/Disable Time Test Circuit and Waveforms



- A. All input pulses are supplied by the Agilent 81250 Parallel BERT Stimulus System with plug-in E4832A.
- B. The cycle-to-cycle jitter measurement is made on a TEK TDS6604 running TDSJIT3 application software.
- C. All other jitter measurements are made with an Agilent Infinium DCA-J 86100C Digital Communications Analyzer.
- D. Period jitter and cycle-to-cycle jitter are measured using a 125MHz $50 \pm 1\%$ duty cycle clock input. Measured over 75K samples.
- E. Deterministic jitter and random jitter are measured using a 250Mbps $2^{15}-1$ PRBS input. Measured over $BER = 10^{-12}$

图 6-4. Receiver Jitter Measurement Waveforms

7 Device Functional Modes

表 7-1. Device Function Table

INPUTS ⁽¹⁾	PDN	FSEN	RE	RECEIVER TYPE	OUTPUT ⁽¹⁾
$V_{ID} = V_A - V_B$					R
$V_{ID} > 35\text{mV}$	H	L	L	Type 1	H
$-35\text{mV} \leq V_{ID} \leq 35\text{mV}$	H	L	L	Type 1	?
$V_{ID} < -35\text{mV}$	H	L	L	Type 1	L
$V_{ID} > 135\text{mV}$	H	H	L	Type 2	H
$65\text{mV} \leq V_{ID} \leq 135\text{mV}$	H	H	L	Type 2	?
$V_{ID} < 65\text{mV}$	H	H	L	Type 2	L
Open Circuit	H	L	L	Type 1	?
Open Circuit	H	H	L	Type 2	L
X	H	X	H	X	Z
X	H	X	OPEN	X	Z
X	L	X	X	X	Z

(1) H=high level, L=low level, Z=high impedance, X=Don't care, ?=indeterminate

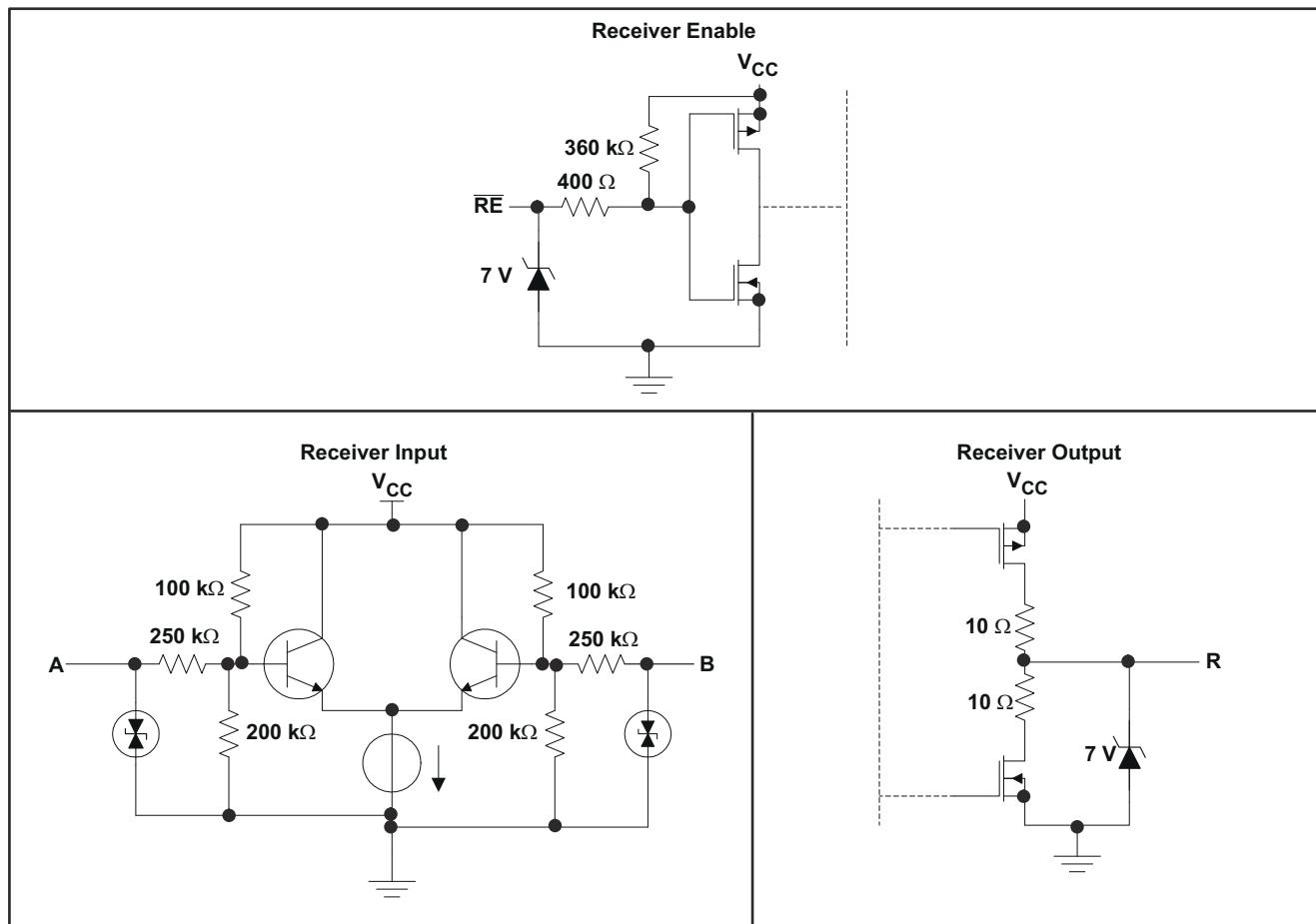


图 7-1. Equivalent Input and Output Schematic Diagrams

8 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

8.1 接收文档更新通知

要接收文档更新通知，请导航至 [ti.com](#) 上的器件产品文件夹。点击 [通知](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

8.2 支持资源

[TI E2E™ 中文支持论坛](#) 是工程师的重要参考资料，可直接从专家处获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题，获得所需的快速设计帮助。

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所有商标均为其各自所有者的财产。

8.4 静电放电警告



静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

8.5 术语表

TI 术语表

本术语表列出并解释了术语、首字母缩略词和定义。

9 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision * (December 2009) to Revision A (March 2024)	Page
• 更改了整个文档中的表格、图和交叉参考的编号格式.....	1

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN65MLVD048RGZR	ACTIVE	VQFN	RGZ	48	2500	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 85	MLVD048	Samples
SN65MLVD048RGZT	ACTIVE	VQFN	RGZ	48	250	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 85	MLVD048	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

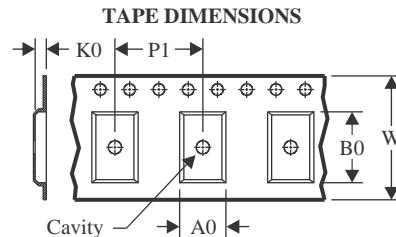
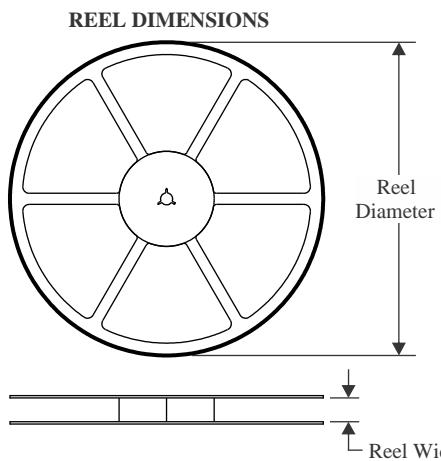
(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

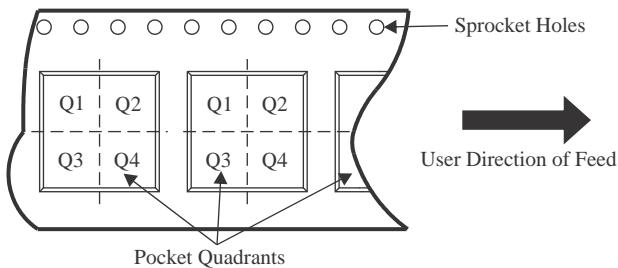
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION



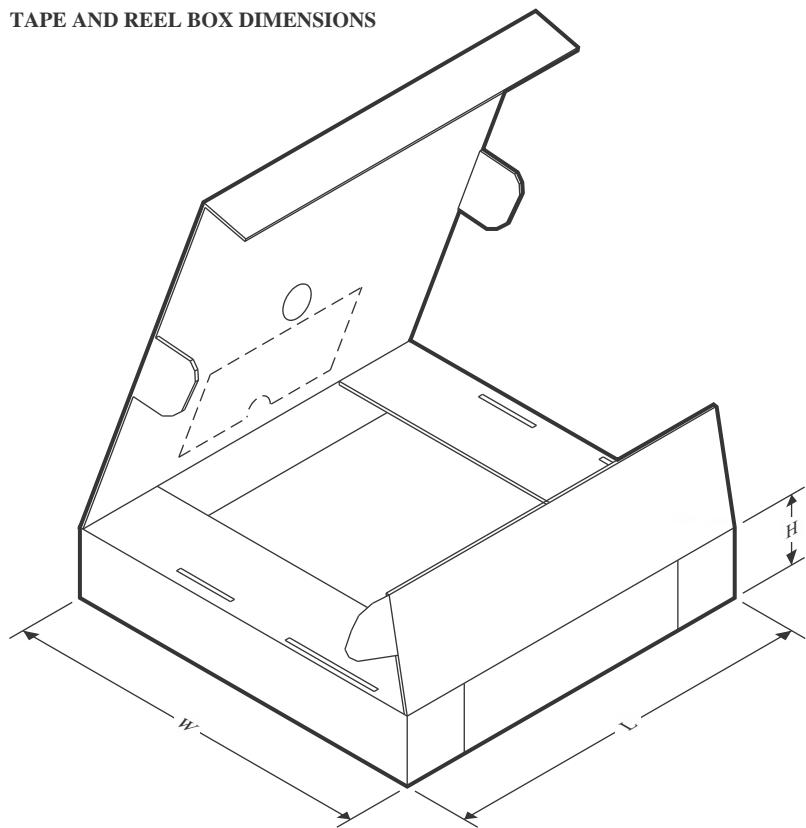
A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65MLVD048RGZR	VQFN	RGZ	48	2500	330.0	16.4	7.3	7.3	1.5	12.0	16.0	Q2
SN65MLVD048RGZT	VQFN	RGZ	48	250	180.0	16.4	7.3	7.3	1.5	12.0	16.0	Q2

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65MLVD048RGZR	VQFN	RGZ	48	2500	356.0	356.0	35.0
SN65MLVD048RGZT	VQFN	RGZ	48	250	210.0	185.0	35.0

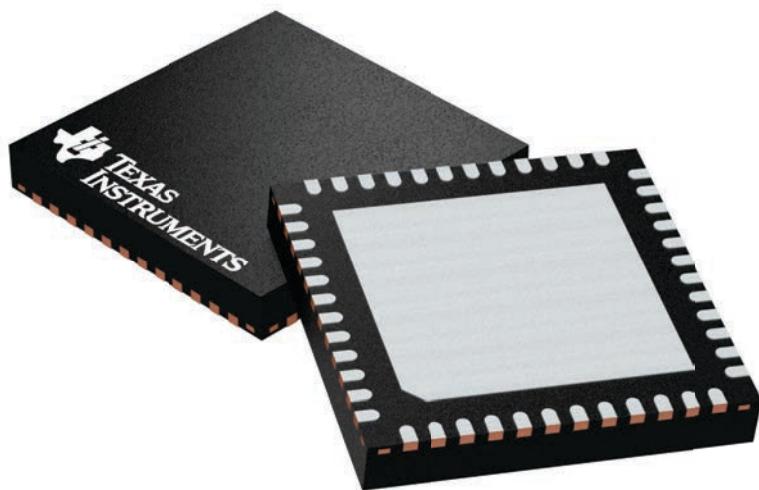
GENERIC PACKAGE VIEW

RGZ 48

VQFN - 1 mm max height

7 x 7, 0.5 mm pitch

PLASTIC QUADFLAT PACK- NO LEAD



Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

4224671/A

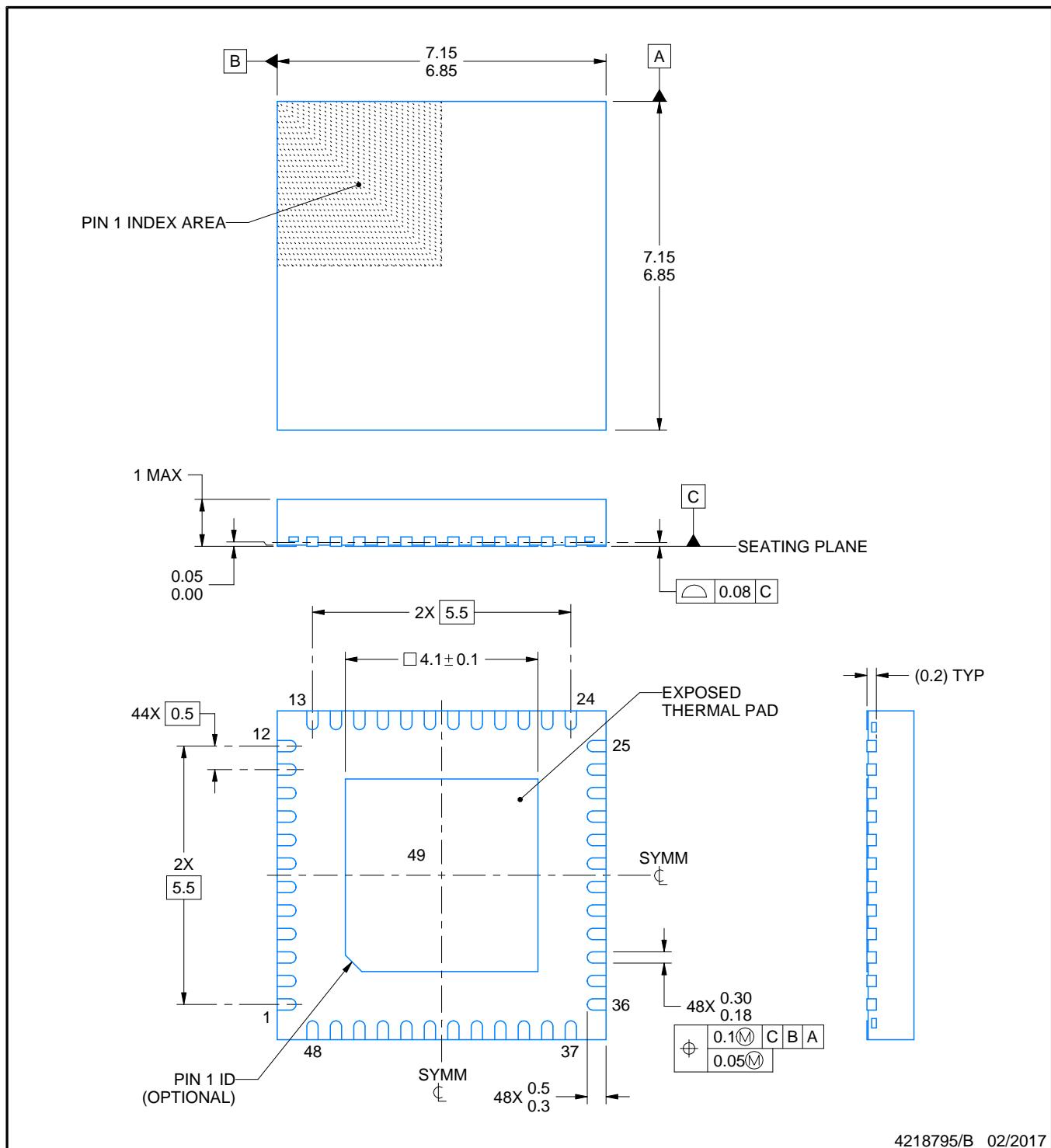
RGZ0048B



PACKAGE OUTLINE

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



4218795/B 02/2017

NOTES:

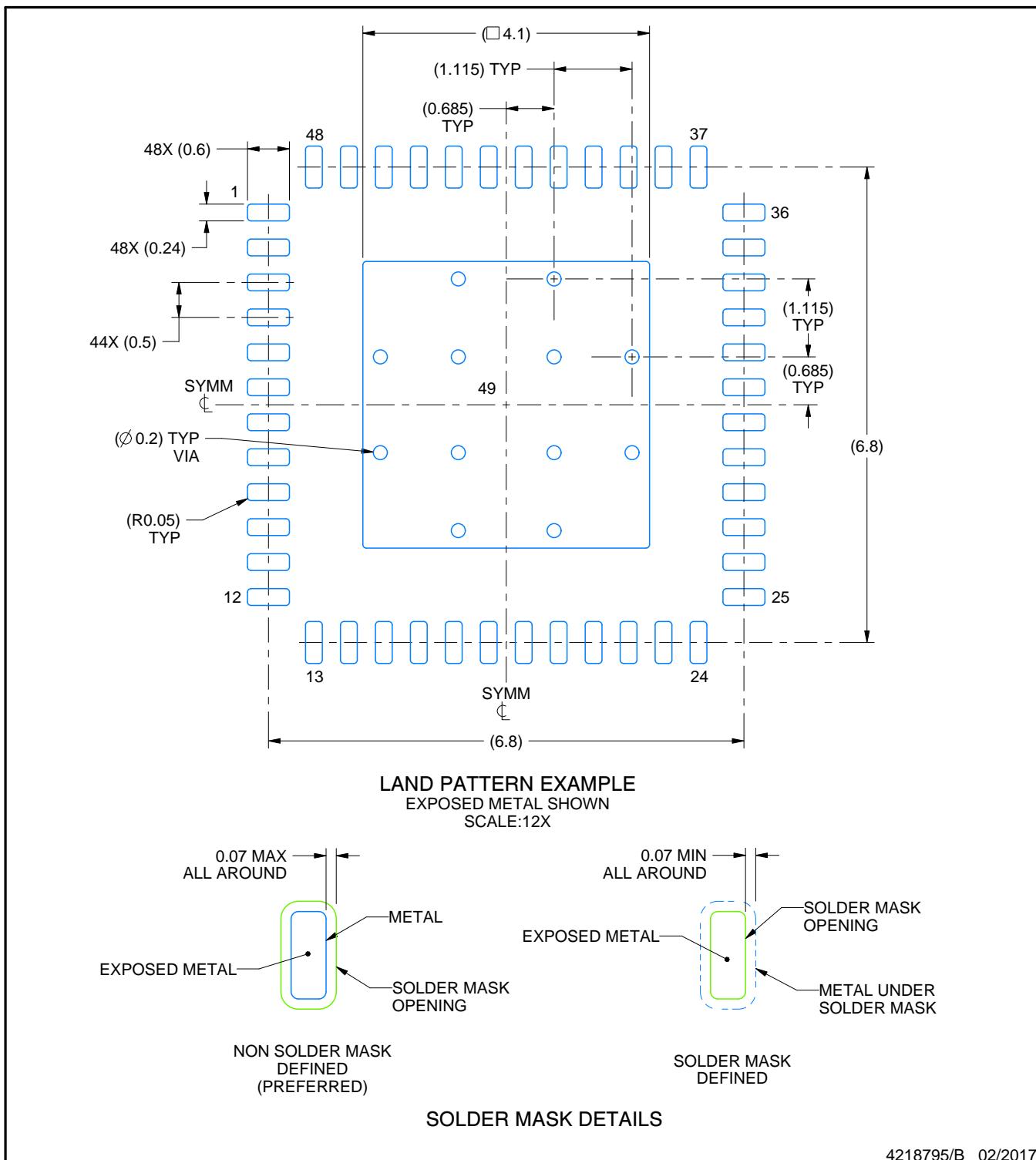
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

EXAMPLE BOARD LAYOUT

RGZ0048B

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

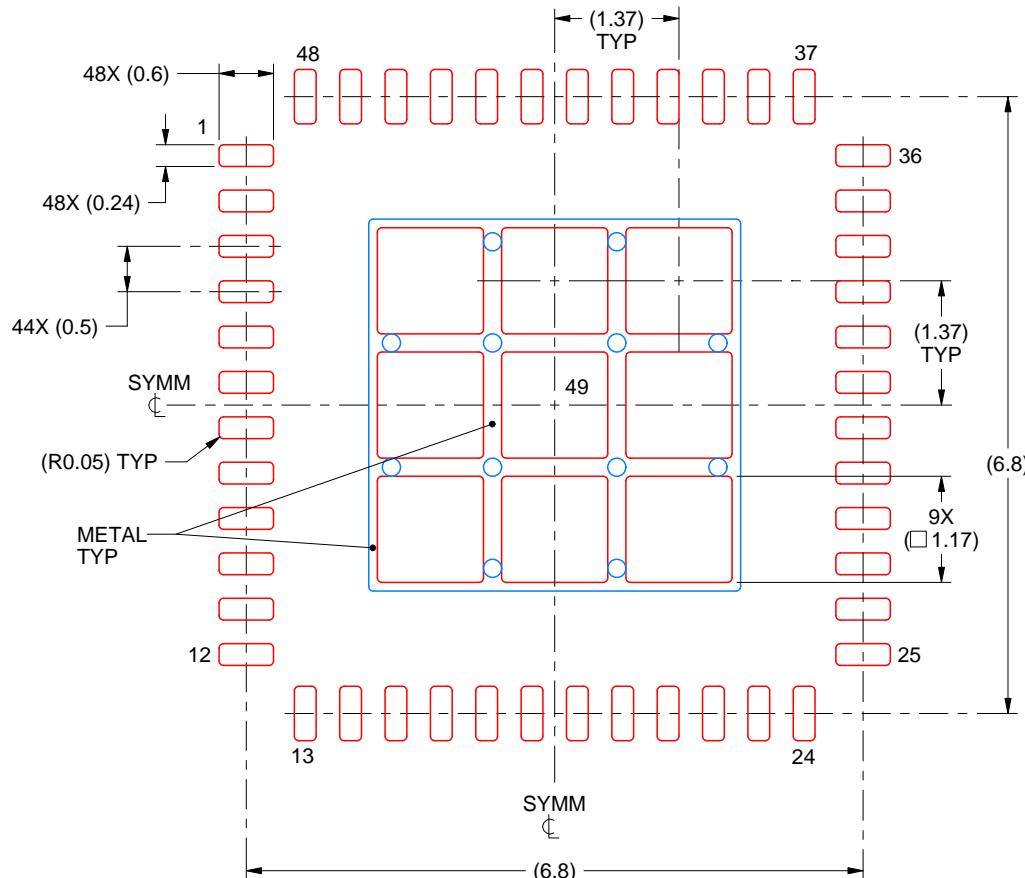
4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

RGZ0048B

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 49
73% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE:12X

4218795/B 02/2017

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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